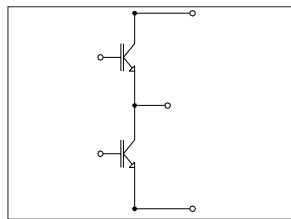


#### Features

- Generation 4 IGBT Technology
- Standard speed: optimized for hard switching operating frequencies up to 1000 Hz
- Very Low Conduction Losses
- Industry standard package



$$V_{CES} = 600V$$

$$V_{CE(on) \text{ typ.}} = 1.13V @$$

$$V_{GE} = 15V, I_C = 200A$$

$$T_J = 25^\circ C$$

#### Benefits

- Increased operating efficiency
- Direct mounting to heatsink
- Performance optimized as output inverter stage for TIG welding machines



#### Absolute Maximum Ratings

Parameters		Max	Units
$V_{CES}$	Collector-to-Emitter Voltage	600	V
$I_C$	Continuos Collector Current	@ $T_C = 25^\circ C$	480
		@ $T_C = 110^\circ C$	220
$I_{CM}$	Pulsed Collector Current	800	
$I_{LM}$	Peak Switching Current	800	
$V_{GE}$	Gate-to-Emitter Voltage	$\pm 20$	V
$V_{ISOL}$	RMS Isolation Voltage, Any Terminal to Case, $t = 1 \text{ min}$	2500	
$P_D$	Maximum Power Dissipation	@ $T_C = 25^\circ C$	830
		@ $T_C = 85^\circ C$	430

Electrical Characteristics @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)

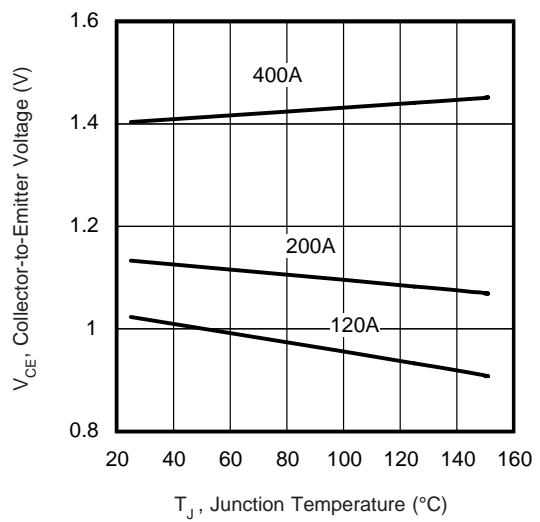
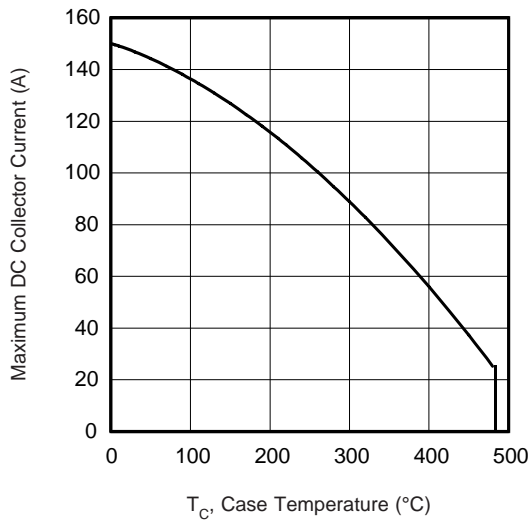
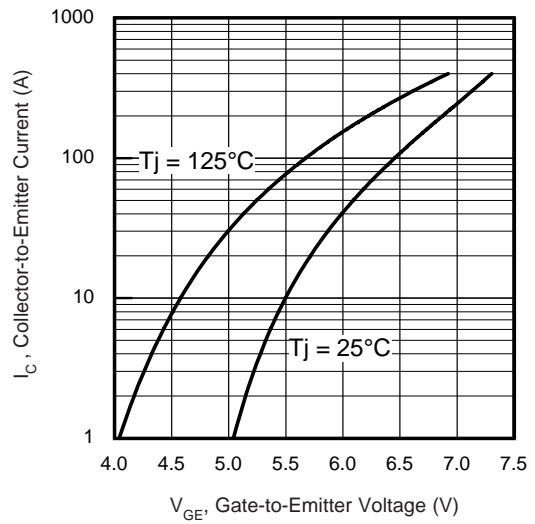
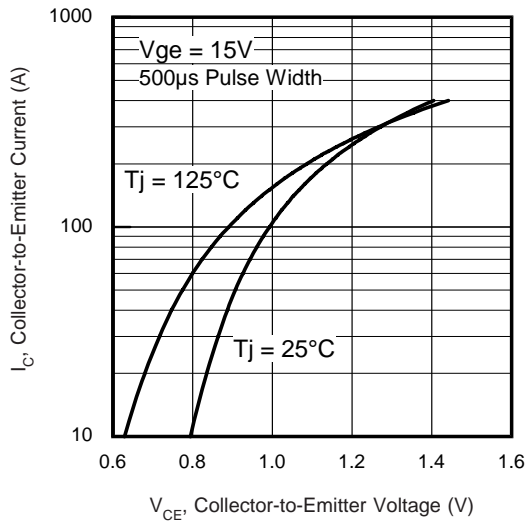
Parameters		Min	Typ	Max	Units	Test Conditions
$V_{CES}$	Collector-to-Emitter Breakdown Voltage	600			V	$V_{GE} = 0V, I_C = 1mA$
$V_{CE(on)}$	Collector-to-Emitter Voltage		1.13	1.21		$V_{GE} = 15V, I_C = 200A$
			1.08	1.18		$V_{GE} = 15V, I_C = 200A, T_J = 125^\circ\text{C}$
$V_{GE(th)}$	Gate Threshold Voltage	3	4.5	6	$I_C = 0.25mA$	
$I_{CES}$	Collector-to-Emitter Leakage Current		0.025	1	mA	$V_{GE} = 0V, V_{CE} = 600V$
				10		$V_{GE} = 0V, V_{CE} = 600V, T_J = 125^\circ\text{C}$
$I_{GES}$	Gate-to-Emitter Leakage Current			$\pm 250$	nA	$V_{GE} = \pm 20V$

Switching Characteristics @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)

Parameters		Min	Typ	Max	Units	Test Conditions
$Q_g$	Total Gate Charge		1600	1700	nC	$I_C = 200A$ $V_{CC} = 400V$ $V_{GE} = 15V$
$Q_{ge}$	Gate-Emitter Charge		260	340		
$Q_{gc}$	Gate-Collector Charge		580	670		
$E_{on}$	Turn-On Switching Loss		30		mJ	$I_C = 200A, V_{CC} = 480V, V_{GE} = 15V$ $R_g = 10\Omega$ free-wheeling DIODE: 30EPH06
$E_{off}$	Turn-Off Switching Loss		50			
$E_{ts}$	Total Switching Loss		80			
$E_{on}$	Turn-On Switching Loss		34		mJ	$I_C = 200A, V_{CC} = 480V, V_{GE} = 15V$ $R_g = 10\Omega$ free-wheeling DIODE: 30EPH06, $T_J = 125^\circ\text{C}$
$E_{off}$	Turn-Off Switching Loss		104			
$E_{ts}$	Total Switching Loss		106	121		
$C_{ies}$	Input Capacitance		32500		pF	$V_{GE} = 0V$ $V_{CC} = 30V$ $f = 1.0\text{ MHz}$
$C_{oes}$	Output Capacitance		2080			
$C_{res}$	Reverse Transfer Capacitance		380			

## Thermal- Mechanical Specifications

Parameters		Min	Typ	Max	Units
$T_J$	Operating Junction Temperature Range	- 40		150	°C
$T_{STG}$	Storage Temperature Range	- 40		125	
$R_{thJC}$	Junction-to-Case (Per Leg)			0.15	°C/ W
$R_{thCS}$	Case-to-Sink		0.1		
T	Mounting torque	Case to heatsink		4	Nm
		Case to terminal 1, 2, 3		3	
	Weight		185		g



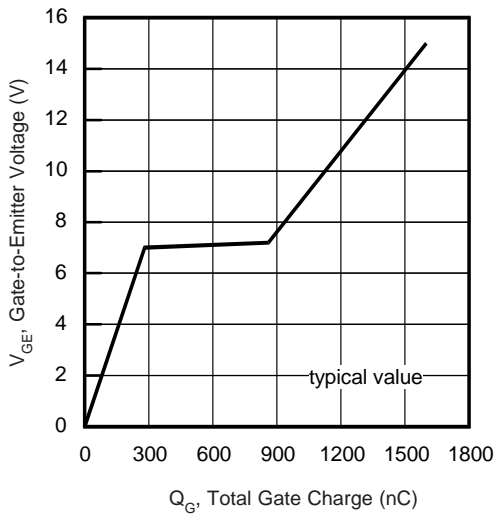


Fig. 5 - Typical Gate Charge vs. Gate-to-Emitter Voltage

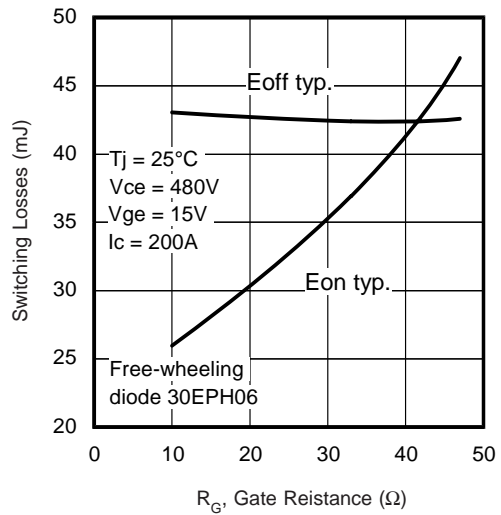


Fig. 6 - Typical Switching Losses vs. Gate Resistance

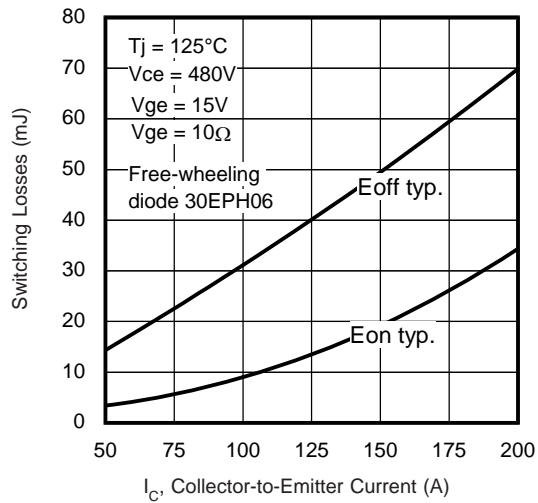
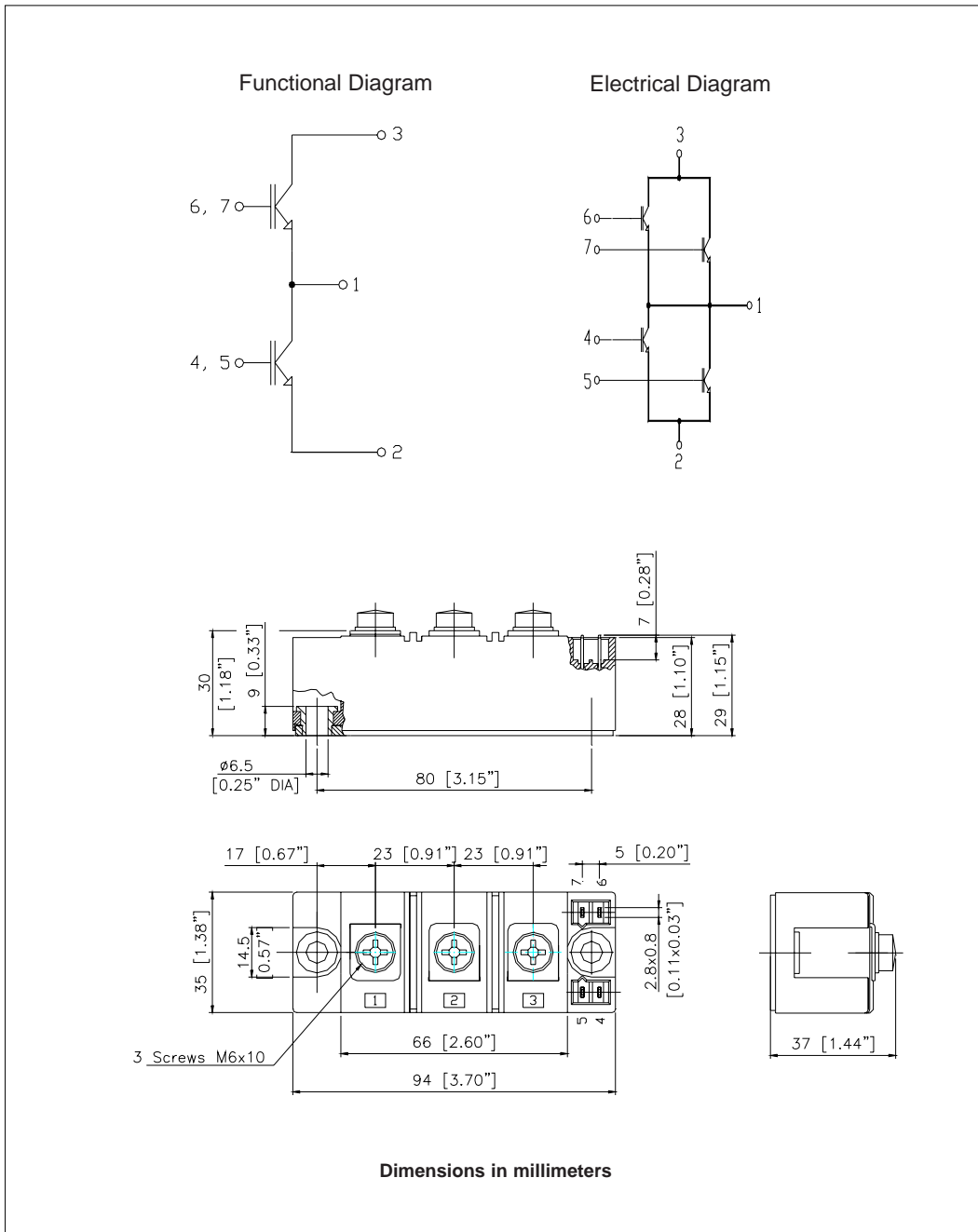


Fig. 7 - Typical Switching Losses vs. Collector-to-Emitter Current

Outline Table



## Ordering Information Table

Device Code															
	<table border="1" style="margin: auto;"> <tr> <td style="padding: 5px;">GA</td> <td style="padding: 5px;">200</td> <td style="padding: 5px;">H</td> <td style="padding: 5px;">S</td> <td style="padding: 5px;">60</td> <td style="padding: 5px;">S</td> <td style="padding: 5px;">1</td> </tr> <tr> <td style="text-align: center;">①</td> <td style="text-align: center;">②</td> <td style="text-align: center;">③</td> <td style="text-align: center;">④</td> <td style="text-align: center;">⑤</td> <td style="text-align: center;">⑥</td> <td style="text-align: center;">⑦</td> </tr> </table>	GA	200	H	S	60	S	1	①	②	③	④	⑤	⑥	⑦
GA	200	H	S	60	S	1									
①	②	③	④	⑤	⑥	⑦									
<b>1</b>	- Essential Part Number IGBT modules														
<b>2</b>	- Current rating (200 = 200A)														
<b>3</b>	- Circuit Configuration (H = Half Bridge without f/w diode)														
<b>4</b>	- Int-A-Pak														
<b>5</b>	- Voltage Code (60 = 600V)														
<b>6</b>	- Speed/ Type (S = Standard Speed IGBT)														
<b>7</b>	- Assy location IRCI														

Data and specifications subject to change without notice.  
 This product has been designed and qualified for Industrial Level.  
 Qualification Standards can be found on IR's Web site.

International  
**IR** Rectifier

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